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10EC63

Sixth Semester B.E. Degree Examination, Dec.2015/Jan.2016 Microelectronics Circuits

Time: 3 hrs.

Max. Marks:100

Note: Answer any FIVE full questions, selecting THREE from PART-A and TWO from PART-B.

PART - A

- 1 a. Explain channel length modulation effect and derive an expression for finite output resistance of a MOSFET in saturation region. (08 Marks)
- b. Analyze the circuit shown in Fig. 1(b) to determine the voltages at all nodes and the currents through all branches let the nMOSFET $V_t = 1V$ and $k'_n \frac{W}{L} = 1mA/V^2$. Assume $\lambda = 0$. (08 Marks)

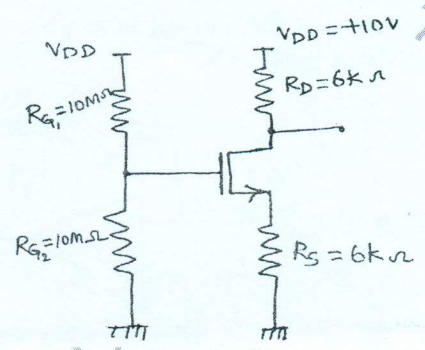


Fig.Q1(b)

- c. Explain briefly biasing using constant current source. (04 Marks)
- 2 a. Derive analytical expressions for transfer characteristics of CS amplifier. (08 Marks)
- b. Fig. Q2(b) shows a discrete CS MOSFET amplifier utilizing the drain to gate feedback biasing arrangement. Determine the small signal voltage. Gain its input resistance and the largest allowable input signal. Let $V_t = 1.5V$, $k'_n \frac{W}{L} = 0.25mA/V^2$ and $V_A = 50V$.

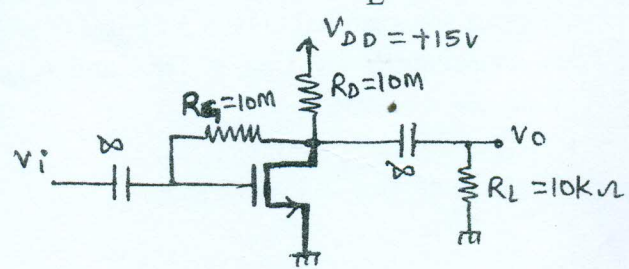


Fig.Q2(b)

- c. Briefly explain common drain amplifier. (05 Marks)
- 3 a. With neat circuit diagram, explain basic BJT current mirror and derive an expression for CT ratio of BJT current mirror for finite β . (08 Marks)
- b. Derive an expression for 3dB frequency f_H for an amplifier having 2 poles and 2 zeros. (08 Marks)
- c. Explain millers theorem. (04 Marks)
- 4 a. Briefly explain common source amplifier with active load. (10 Marks)
- b. With neat circuit diagram, explain the MOS cascode amplifier. (10 Marks)

Important Note : 1. On completing your answers, comparatively draw diagonal cross lines on the remaining blank pages. 2. Any revealing of identification, appeal to evaluator and /or equations written eg. 42+8 = 50, will be treated as malpractice.



PART - B

- 5 a. Explain the operation of MOS differential pair with a common mode input voltage. (07 Marks)
- b. Briefly explain the basic operation of BJT differential pair with neat circuit diagram. (07 Marks)
- c. Explain two stage CMOS OPAMP. (06 Marks)
- 6 a. Write a note on gain desensitivity and bandwidth extension. (06 Marks)
- b. Draw the ideal structure and equivalent circuit of the series shunt feedback amplifier and explain. (10 Marks)
- c. Write a note on amplifier with a single pole response. (04 Marks)
- 7 A Derive an expression for the closed load gain (v_o/v_i) of the circuit shown in Fig. Q7(a). Assume the OPAMP is ideal. (06 Marks)

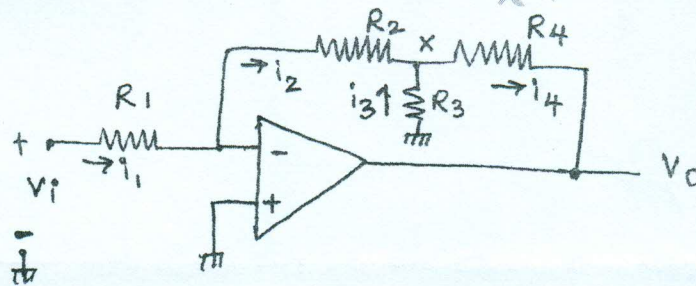


Fig.Q7(a)

- b. Explain instrumentation amplifier with neat circuit diagram. (08 Marks)
- c. With neat circuit diagram, explain antilog amplifier. (06 Marks)
- 8 a. A CMOS inverter fabricated in a $0.25 \mu\text{m}$ process has $C_{ox} = 6 \text{ fF}/\mu\text{m}^2$, $\mu_n C_{ox} = 115 \mu\text{A}/\text{V}^2$, $\mu_p C_{ox} = 30 \mu\text{A}/\text{V}^2$, $v_{tn} = -v_{tp} = 0.4\text{V}$ and $V_{DD} = 2.5\text{V}$. The W/L ratio of Q_n is $0.375 \mu\text{m}/0.25 \mu\text{m}$, and that for Q_p is $1.125 \mu\text{m}/0.25 \mu\text{m}$. The gate - source and gate drain overlap capacitances are specified to be $0.3 \text{ fF}/\mu\text{m}$ of gate width. Further the effective value of drain body capacitances are $C_{dbn} = 1\text{fF}$ and $C_{dbp} = 1 \text{ fF}$. The wiring capacitance $C_w = 0.2\text{fF}$. Find t_{PHL} , t_{PLH} and t_p . (10 Marks)
- b. Implement $F = AB + \overline{AB}$ using AOI. (05 Marks)
- c. Explain two single input domino CMOS gate. (05 Marks)
